

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) A liquid crystal display device produced by the process of claim 8[[,]] comprising:

a substrate;

a gate electrode over the substrate;

a first semiconductor layer over the gate electrode;

a second semiconductor layer over the first semiconductor layer and having a defined outer edge;

a first metal layer on the second semiconductor layer and having a defined outer edge, the first metal layer patterned in a same pattern as the second semiconductor layer such that the defined outer edge of the first metal layer is lined up with the defined outer edge of the second semiconductor layer to define a separation region; and

source and drain electrodes over the first metal layer, ~~the source and drain electrodes adapted to be used to pattern by etching the semiconductor layers in the same pattern as the first metal layer to reduce over etching of the first metal layer and~~ to define a first upper portion of the separation region that abuts the lined up outer edges of the first and second semiconductor layers, and the source and drain electrodes include a second and a third metal layer.

2. (Original) The device of claim 1, further comprising:

an insulating layer in between the gate electrode and the first semiconductor layer;

a protective layer over the source and drain electrodes and defining a second upper portion of the separation region and a contact hole exposing a portion of the drain electrode; and a pixel electrode in the contact hole.

3. (Previously Presented) The device of claim 1, wherein the second metal layer includes aluminum or an aluminum alloy.

4. (Original) The device of claim 1, wherein the first and third metal layers are formed of the same material.

5. (Original) The device of claim 1, wherein the first and third metal layers are formed of different materials.

6. (Original) The device of claim 1, wherein the first and third metal layers include titanium, tungsten, tantalum, chromium or molybdenum.

7. (Original) The device of claim 4, wherein the first and third metal layers include titanium, tungsten, tantalum, chromium or molybdenum.

8. (Currently Amended) A method of forming a liquid crystal display device, comprising:

forming a gate electrode on a substrate;

forming an active layer over the gate electrode;

forming a first semiconductor layer over the active layer;

forming a second semiconductor layer over the first semiconductor layer and having a defined outer edge;

forming a first metal layer having a defined outer edge over the second semiconductor layer;

forming and patterning a source electrode and a drain electrode over the first metal layer using a wet etch process; and

forming and patterning the first metal layer and the second semiconductor layer in a same pattern by dry-etching using the source and drain electrodes as a mask to expose the active layer between the source and drain electrodes such that the defined outer edge of the first metal layer is lined up with the defined outer edge of the second semiconductor layer to define a separation region and to reduce over-etching of the first metal layer.

9. (Original) The method of claim 8, wherein

forming the source and drain electrodes includes

forming a second metal layer over the first metal layer,

forming a third metal layer over the first metal layer, and

patterning the second and third metal layers in the same pattern as the first metal layer and second semiconductor layer in the channel region so that a channel portion of the first semiconductor layer is exposed.

10. (Original) The method of claim 8, wherein  
the first metal layer is formed of titanium, tungsten, tantalum, chromium or molybdenum.

11. (Original) The method of claim 9, wherein  
the first and third metal layers are formed of the same material.

12. (Original) The method of claim 9, wherein  
the first and third metal layers are formed of a different material.

13. (Original) The method of claim 9, wherein  
the second metal layer is formed of aluminum or an aluminum alloy.

14. (Original) The method of claim 9, wherein  
the first and third metal layers are formed of titanium, tungsten, tantalum, chromium or molybdenum.

15. (Original) The method of claim 8, wherein  
the patterning of the first metal layer and the second semiconductor layer to define a channel region includes removing a portion of the first metal layer and second metal layer corresponding to the gate electrode and exposing the first semiconductor layer.

16-20. (Canceled)

21. (Currently Amended) A method of forming a liquid crystal display device,  
comprising:

forming a gate electrode on a substrate;  
forming an active layer over the gate electrode;  
forming a first semiconductor layer over the active layer;  
forming a second semiconductor layer over the first semiconductor layer and having a defined outer edge;  
forming a first metal layer having a defined outer edge over the second semiconductor layer;  
forming and patterning a source electrode and a drain electrode over the first metal layer  
by a wet-etch process;  
forming an ohmic contact layer on the second semiconductor layer; and  
patterning, simultaneously, the first metal layer, the second semiconductor layer, and the ohmic contact layer in a same pattern by dry-etching using the source and drain electrodes as a mask to expose the active layer between the source and drain electrodes such that the defined

outer edge of the first metal layer is lined up with the defined outer edge of the second semiconductor layer to define a separation region and to reduce over-etching of the first metal layer.

22. (New) A liquid crystal display device produced by the process of claim 21.